

# MOSFET – N-Channel, POWERTRENCH<sup>®</sup>, DUAL COOL<sup>®</sup> 88

60 V, 292 A, 1.1 mΩ

## FDMT80060DC

### General Description

This N-Channel MOSFET is produced using onsemi's advanced POWERTRENCH process. Advancements in both silicon and DUAL COOL package technologies have been combined to offer the lowest  $r_{DS(on)}$  while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance.

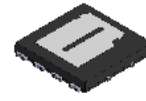
### Features

- Max  $r_{DS(on)}$  = 1.1 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 43\text{ A}$
- Max  $r_{DS(on)}$  = 1.3 mΩ at  $V_{GS} = 8\text{ V}$ ,  $I_D = 37\text{ A}$
- Advanced Package and Silicon Combination for Low  $r_{DS(on)}$  and High Efficiency
- Next Generation Enhanced Body Diode Technology, Engineered for Soft Recovery
- Low Profile 8x8 mm MLP Package
- MSL1 Robust Package Design
- 100% UIL Tested
- This Device is Pb-Free, Halide Free and RoHS Compliant

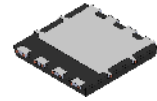
### Applications

- OringFET / Load Switching
- Synchronous Rectification
- DC-DC Conversion

$V_{DS}$	$r_{DS(on)}$ MAX	$I_D$ MAX
60 V	1.1 mΩ @ 10 V	292 A
	1.3 mΩ @ 8 V	



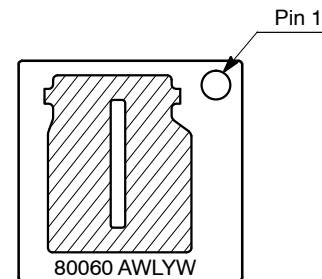
Top



Bottom

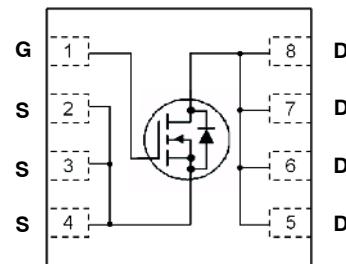
TDFNW8 8.3x8.4, 2P,  
DUAL COOL, OPTION 2  
CASE 507AR

### MARKING DIAGRAM



80060 = Device Code  
A = Assembly Location  
WL = Wafer Lot Code  
Y = Year Code  
W = Work Week Code

### ELECTRICAL CONNECTION



N-Channel MOSFET

### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 7 of this data sheet.

# FDMT80060DC

## MOSFET MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DS}$	Drain to Source Voltage	60	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current –Continuous $T_C = 25^\circ\text{C}$ (Note 5)	292	A
	–Continuous $T_C = 100^\circ\text{C}$ (Note 5)	184	
	–Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	43	
	–Pulsed (Note 4)	1825	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	2400	mJ
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$	156	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	3.2	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top Source)	1.6	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Bottom Drain)	0.8	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	38	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	81	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1i)	15	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1j)	21	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1k)	9	

# FDMT80060DC

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	60	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25°C	–	30	–	mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V	–	–	1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	–	–	±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	2.0	3.5	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25°C	–	–13	–	mV/°C
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 43 A	–	0.87	1.1	mΩ
		V <sub>GS</sub> = 8 V, I <sub>D</sub> = 37 A	–	1.1	1.3	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 43 A, T <sub>J</sub> = 125°C	–	1.3	1.7	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 43 A	–	134	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz	–	14406	20170	pF
C <sub>oss</sub>	Output Capacitance		–	3222	4515	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	87	175	pF
R <sub>g</sub>	Gate Resistance		0.1	1.8	4.5	Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 43 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω	–	75	120	ns
t <sub>r</sub>	Rise Time		–	47	76	
t <sub>d(off)</sub>	Turn-Off Delay Time		–	66	106	
t <sub>f</sub>	Fall Time		–	19	34	
Q <sub>g(TOT)</sub>	Total Gate Charge	V <sub>GS</sub> = 0 V to 10 V, V <sub>DD</sub> = 30 V, I <sub>D</sub> = 43 A	–	170	238	nC
		V <sub>GS</sub> = 0 V to 8 V, V <sub>DD</sub> = 30 V, I <sub>D</sub> = 43 A	–	137	192	
Q <sub>gs</sub>	Gate to Source Charge	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 43 A	–	71	–	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge		–	19	–	nC

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.6 A (Note 2)	–	0.7	1.1	V
		V <sub>GS</sub> = 0 V, I <sub>S</sub> = 43 A (Note 2)	–	0.8	1.2	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 43 A, di/dt = 100 A/μs	–	84	135	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	89	143	nC

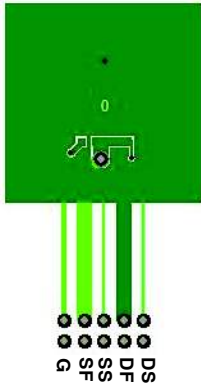
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**THERMAL CHARACTERISTICS**

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top Source)	1.6	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Bottom Drain)	0.8	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	38	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	81	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1c)	26	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1d)	34	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1e)	14	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1f)	16	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1g)	26	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1h)	60	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1i)	15	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1j)	21	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1k)	9	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1l)	11	

**NOTES:**

- $R_{\theta JA}$  is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below.  $R_{\theta CA}$  is determined by the user's board design.



a) 38°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b) 81°C/W when mounted on a minimum pad of 2 oz copper.

- Still air, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- Still air, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, minimum pad of 2 oz copper
- Still air, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- Still air, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper
- 200 FPM Airflow, No Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- 200 FPM Airflow, No Heat Sink, minimum pad of 2 oz copper
- 200 FPM Airflow, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- 200 FPM Airflow, 20.9 × 10.4 × 12.7 mm Aluminum Heat Sink, minimum pad of 2 oz copper
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- 200 FPM Airflow, 45.2 × 41.4 × 11.7 mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
- $E_{AS}$  of 2400 mJ is based on starting  $T_J = 25^\circ\text{C}$ ; N-ch:  $L = 3\text{ mH}$ ,  $I_{AS} = 40\text{ A}$ ,  $V_{DD} = 60\text{ V}$ ,  $V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.3\text{ mH}$ ,  $I_{AS} = 87\text{ A}$ .
- Pulsed Id please refer to Figure 11 SOA graph for more details.
- Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

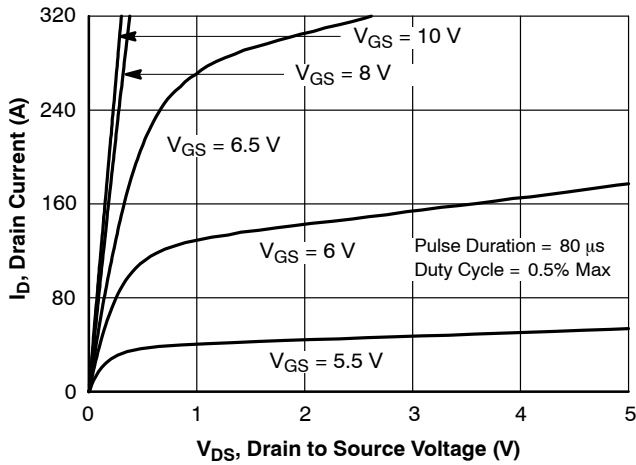


Figure 1. On Region Characteristics

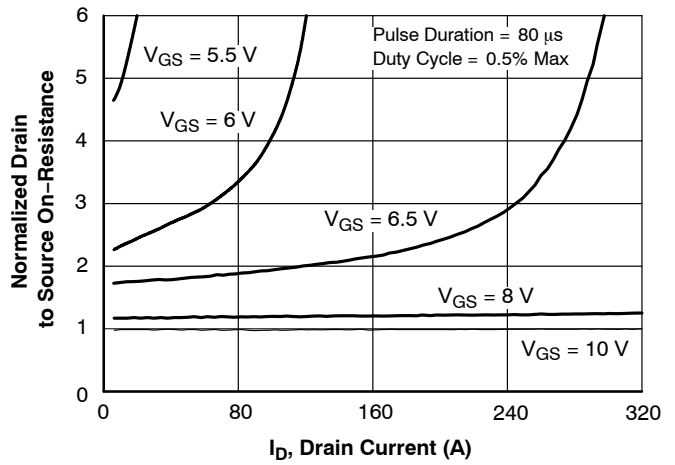


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

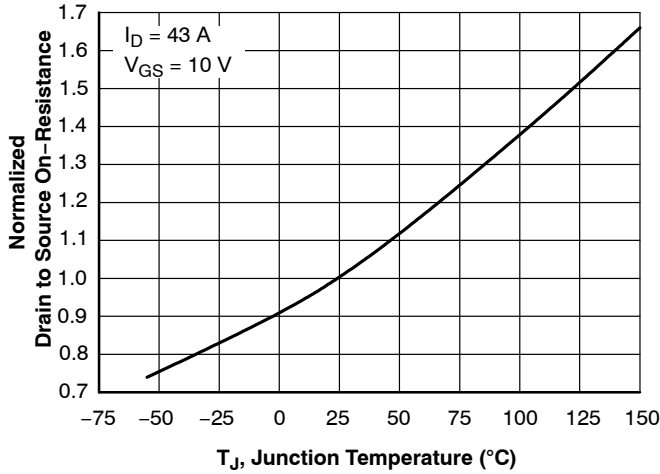


Figure 3. Normalized On Resistance vs. Junction Temperature

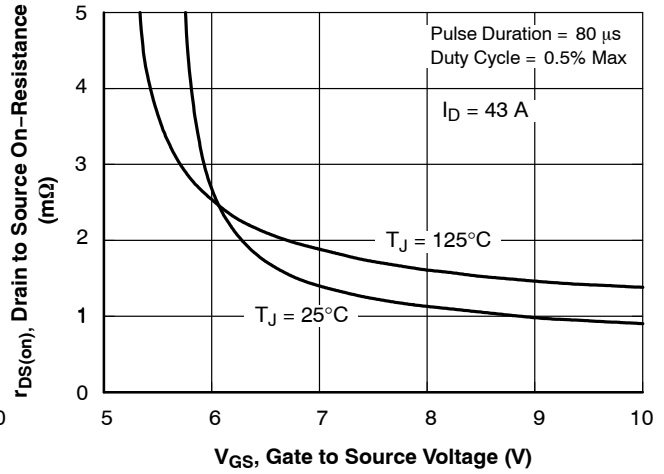


Figure 4. On-Resistance vs. Gate to Source Voltage

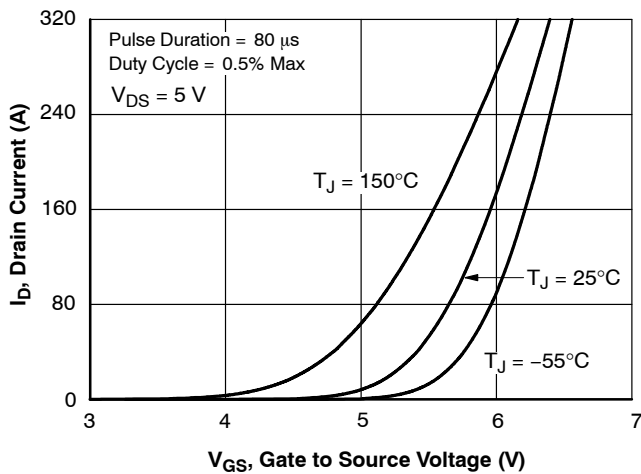


Figure 5. Transfer Characteristics

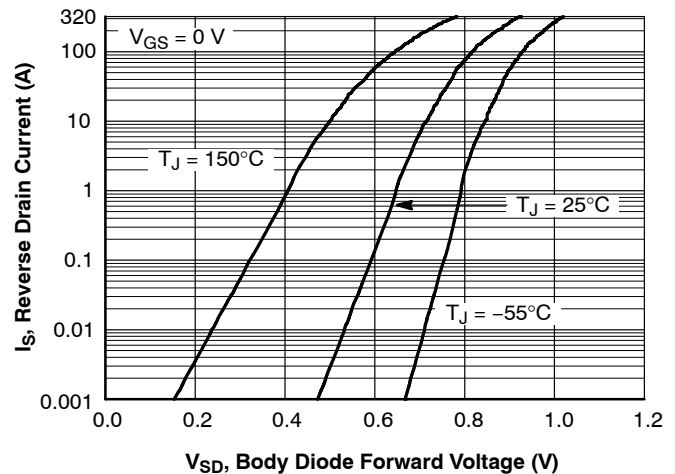


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted) (continued)

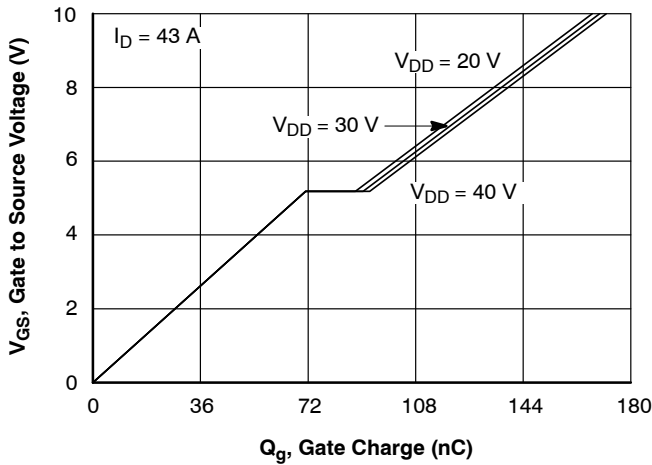


Figure 7. Gate Charge Characteristics

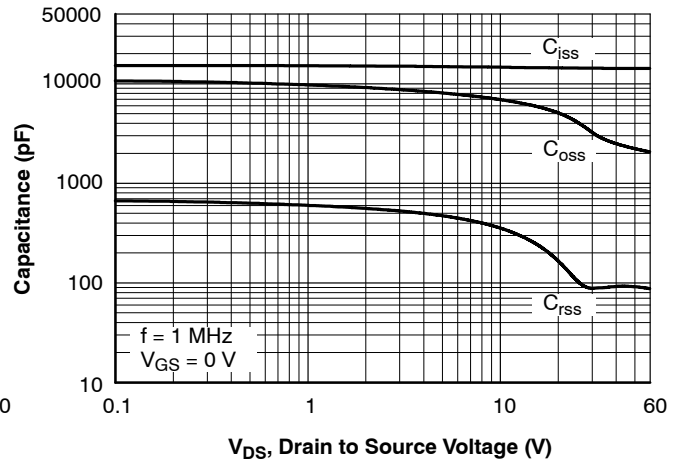


Figure 8. Capacitance vs. Drain to Source Voltage

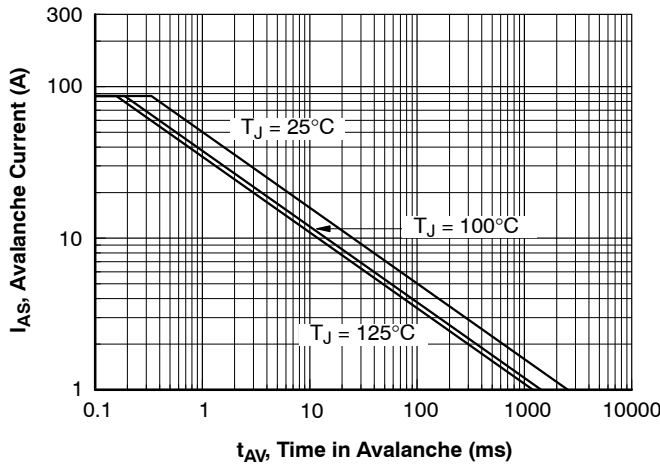


Figure 9. Unclamped Inductive Switching Capability

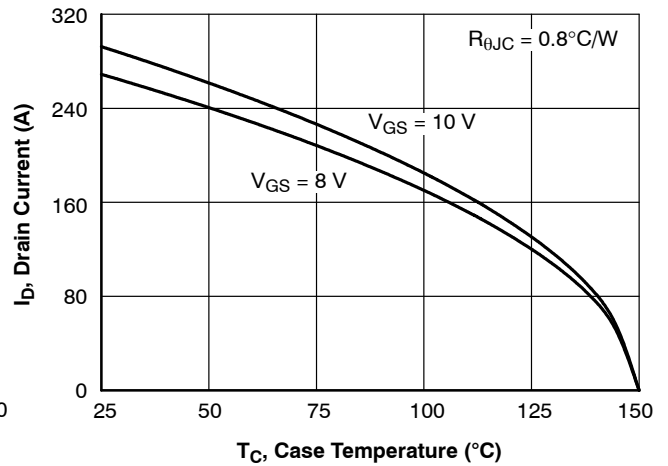


Figure 10. Maximum Continuous Drain Current vs Case Temperature

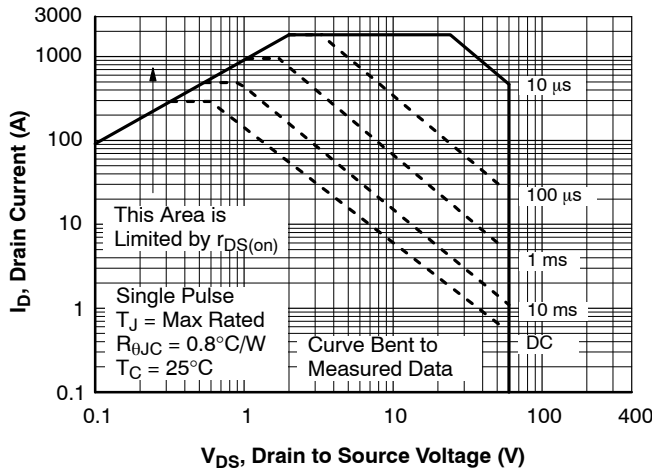


Figure 11. Forward Bias Safe Operating Area

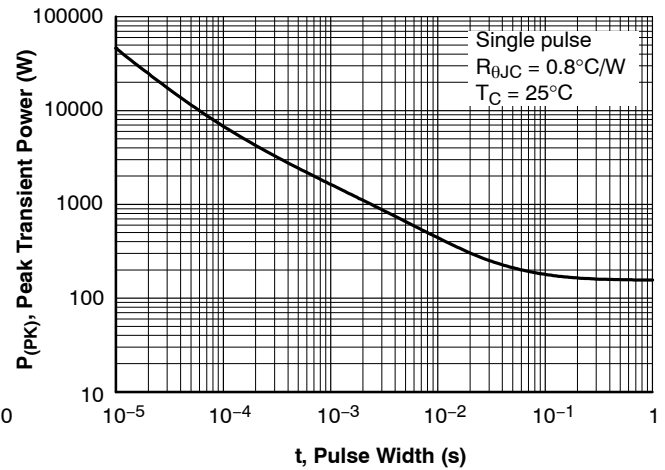


Figure 12. Single Pulse Maximum Power Dissipation

# FDMT80060DC

## TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

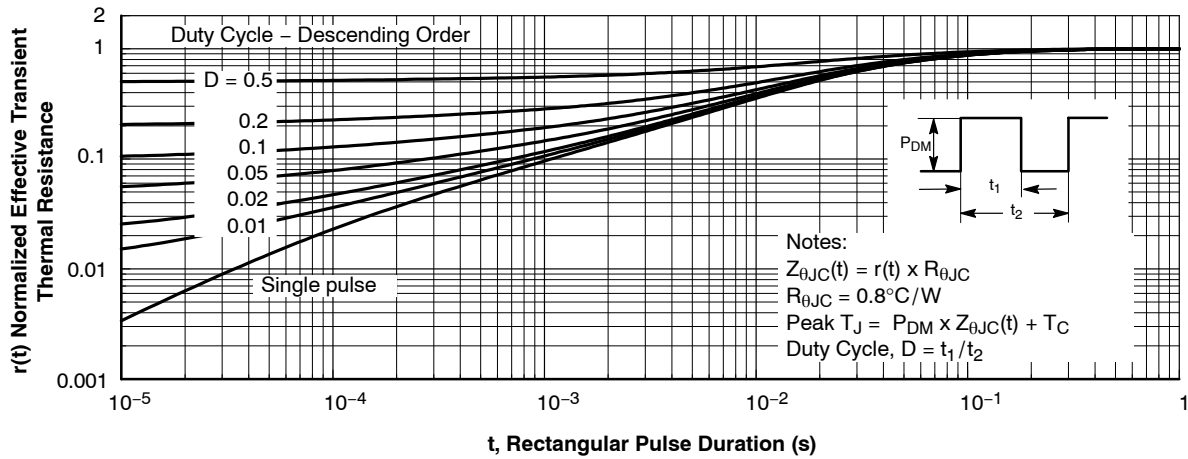


Figure 13. Junction-to-Case Transient Thermal Response Curve

### PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Reel Size	Tape Width	Shipping <sup>†</sup>
80060	FDMT80060DC	TDFNW8 8.3x8.4, 2P, DUAL COOL, OPTION 2	13"	13.3 mm	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

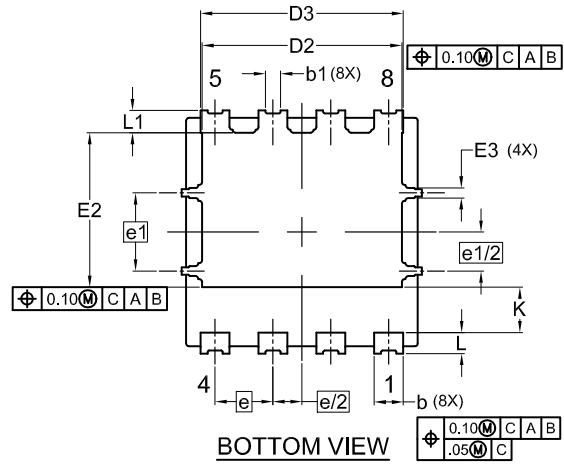
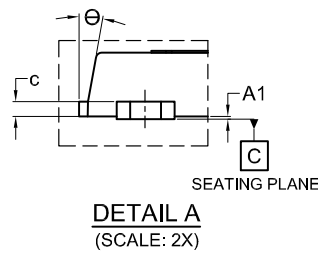
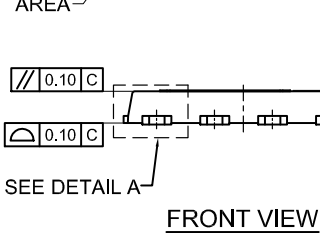
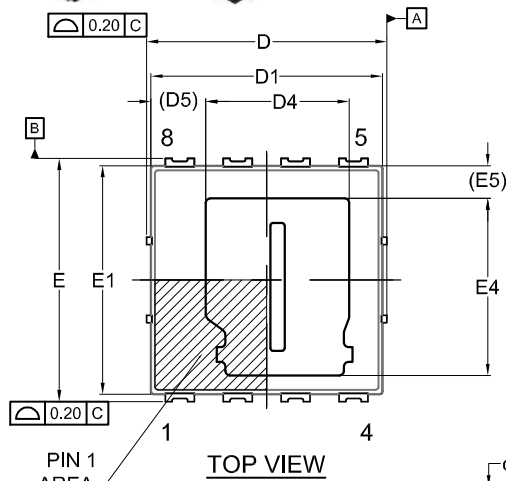
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®

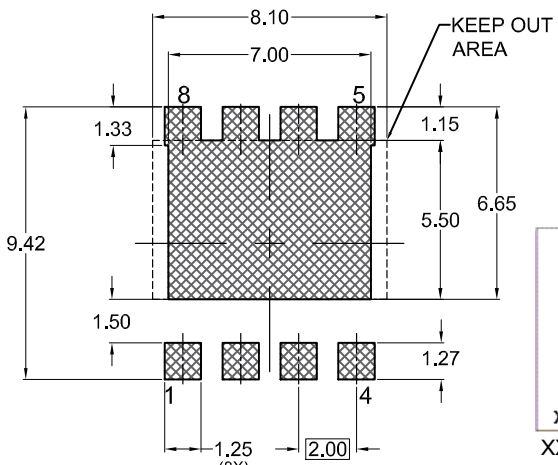


## TDFNW8 8.3x8.4, 2P, DUAL COOL, OPTION 2 CASE 507AR ISSUE B

DATE 29 MAR 2021



- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M, 2009.
  2. CONTROLLING DIMENSION: MILLIMETERS
  3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
  4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
  5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



**RECOMMENDED LAND PATTERN**

(For additional information on our Pb-free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.)



- XXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot Code
- Y = Year Code
- W = Work Week Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.82	0.92	1.02
A1	0.00	--	0.05
b	0.90	1.00	1.10
b1	0.35	0.45	0.55
c	0.23	0.28	0.33
D	8.20	8.30	8.40
D1	7.90	8.00	8.10
D2	6.80	6.90	7.00
D3	6.90	7.00	7.10
D4	4.90	5.05	5.20
D5	1.85 REF		
E	8.30	8.40	8.50
E1	7.80	7.90	8.00
E2	5.24	5.34	5.44
E3	0.25	0.35	0.45
E4	6.08	6.23	6.38
E5	1.13 REF		
e	2.00 BSC		
e/2	1.00 BSC		
e1	2.70 BSC		
e1/2	1.35 BSC		
K	1.50	1.57	1.70
L	0.64	0.74	0.84
L1	0.67	0.77	0.87
θ	0°	--	12°

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<b>DESCRIPTION:</b>	<b>TDFNW8 8.3x8.4, 2P, DUAL COOL, OPTION 2</b>	<b>PAGE 1 OF 1</b>

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